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(71) Applicant (for all designated States except US): **AGENCY FOR SCIENCE, TECHNOLOGY AND RESEARCH** [SG/SG]; 1 Fusionopolis Way, #20-10 Connexis, Singapore 138632 (SG).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **ORATTI KALANDAR, Navas, Khan** [IN/SG]; Institute of Microelectronics, 11 Science Park Road, Singapore Science Park 2, Singapore 117685 (SG). **KRIPESH, Vaidyanathan** [IN/SG]; Institute of Microelectronics, 11 Science Park Road, Singapore Science Park 2, Singapore 117685 (SG). **ZHANG, Xiaowu** [SG/SG]; Institute of Microelectronics, 11 Science Park Road, Singapore Science Park 2, Singapore 117685 (SG). **KHONG, Chee Houe** [SG/SG]; Institute of Microelectronics, 11 Science Park Road, Singapore Science Park 2, Singapore 117685 (SG).

(74) Agent: **SCHIWECK, Wolfram**; Viering, Jentschura & Partner LLP, P.O. Box 1088, Rochor Post Office, Rochor Road, Singapore 911833 (SG).

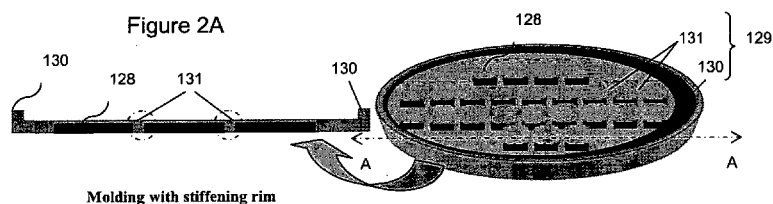
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(54) Title: A SEMICONDUCTOR STRUCTURE AND A METHOD OF MANUFACTURING A SEMICONDUCTOR STRUCTURE



(57) Abstract: According to one embodiment of the present invention, a semiconductor structure is provided. The semiconductor structure includes a first support structure, a plurality of chips formed on the first support structure and a reinforcing structure formed on the first support structure, the reinforcing structure including an outer surrounding element which surrounds the plurality of chips and extends from a surface of the first support structure to a height higher than each of the plurality of chips. A method of manufacturing a semiconductor structure is also provided.